

2SC1815LT1

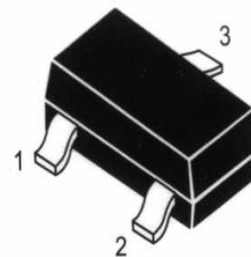
NPN EPITAXIAL SILICON TRANSISTOR

- * Complement to 2SA1015
- * Collector Current :Ic=150mA

ABSOLUTE MAXIMUM RATINGS at Ta=25℃

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	Vcbo	60	V
Collector-Emitter Voltage	Vceo	50	V
Emitter-Base Voltage	Vebo	5	V
Collector Current	Ic	150	mA
Collector Dissipation Ta=25℃*	P _D	225	mW
Junction Temperature	T _j	150	℃
Storage Temperature	Tstg	-55-150	℃

Package:SOT-23



PIN:	1	2	3
STYLE			
NO.1	B	E	C

ELECTRICAL CHARACTERISTICS at Ta=25℃

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BVcbo	60			V	Ic=100uA Ic=0
Collector-Emitter Breakdown Voltage#	BVceo	50			V	Ic= 1mA Ib=0
Emitter-Base Breakdown Voltage	BVebo	5.0			V	Ie= 100uA Ic=0
Collector-Base Cutoff Current	Icbo			100	nA	Vcb= 50V Ie=0
Emitter-Base Cutoff Current	Iebo			100	nA	Veb= 3V Ic= 0
DC Current Gain	Hfe	70		700		Vce= 6V Ic= 2mA
Collector-Emitter Saturation Voltage	Vce(sat)			0.30	V	Ic= 100mA Ib= 10mA

* Total Device Dissipation : FR=1x0.75x0.062in Board,Derate 25℃.

Pulse Test : Pulse Width ≤300uS,Duty cycle ≤2%

DEVICE MARKING:

2SC1815=L6